DATASHEET

1.9mm Round Subminiature “Gull Wing”Lead Phototransistor

PT91-21B/L41/TR7

Features

- Fast response time
- High photo sensitivity
- Small junction capacitance
- Compatible with infrared and vapor phase reflow solder process.
- Pb free
- The product itself will remain within RoHS compliant version.
- Compliance with EU REACH.
- Compliance Halogen Free .(Br <900 ppm ,Cl <900 ppm , Br+Cl < 1500 ppm).

Descriptions

- PT91-21B/L41/TR7 is a phototransistor in miniature SMD package which is molded in water clear plastic with spherical top view lens. The device is spectrally matched to infrared emitting diode.

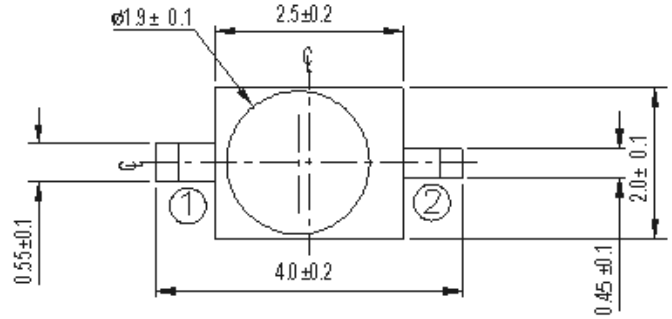
Applications

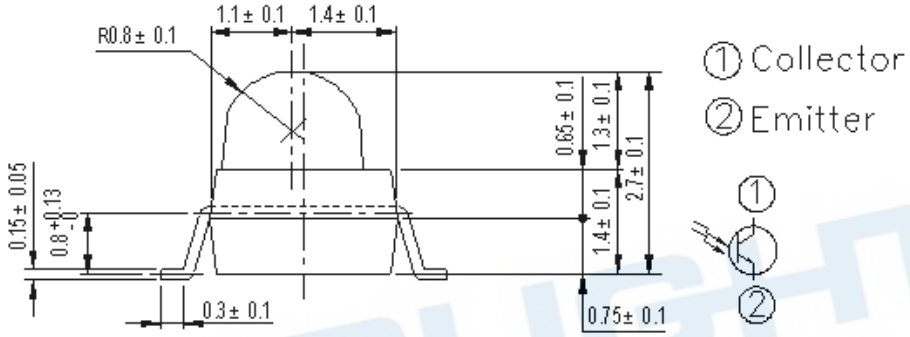
- Miniature switch
- Counters and sorter
- Position sensor
- Infrared applied system

Device Selection Guide

Part Category	Chip Material	Lens Color
PT	Silicon	Black clear

Package Dimensions





Notes: 1.All dimensions are in millimeters
2.Tolerances unless dimensions ±0.1mm

Absolute Maximum Ratings (Ta=25℃)

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector-Voltage	V_{ECO}	5	V
Collector Current	I_C	20	mA
Operating Temperature	T_{opr}	-25 ~ +85	℃
Storage Temperature	T_{stg}	-40 ~ +85	℃
Soldering Temperature *1	T_{sol}	260	℃
Power Dissipation at(or below) 25℃ Free Air Temperature	P_d	75	mW

Notes: *1:Soldering time≦5 seconds.

Electro-Optical Characteristics (Ta=25℃)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Rang Of Spectral Bandwidth	$\lambda_{0.5}$	---	700	---	1100	nm
Wavelength Of Peak Sensitivity	λ_P	---	---	940	---	nm
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=100μA Ee=0mW/cm^2	30	---	---	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	I_E=100μA Ee=0mW/cm^2	5	---	---	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2mA Ee=1mW/cm^2	---	---	0.4	V
Collector Dark Current	I_{CEO}	V_{CE}=20V Ee=0mW/cm^2	---	---	100	nA
On State Collector Current	$I_{C(ON)}$	V_{CE}=5V Ee=1mW/cm^2 λP=940nm	2.0	---	6.0	mA
Rise Time	Tr	V_{CE}=5V I_C=1mA R_L=1000Ω	---	15	---	us
Fall Time	Tf		---	15	---	

Intensity Specifications for Bin Grading

Rank	Test Condition	Min	Max	Unit
BIN3	V_{CE}=5V Ee=1mW/cm^2 λP=940nm	2.0	4.0	mA
BIN4		2.5	5.0	
BIN5		3.0	6.0	

Notes: This bin table is only for reference, not for specific bin shipment.

Typical Electro-Optical Characteristics Curves

Fig.1 Spectral Sensitivity

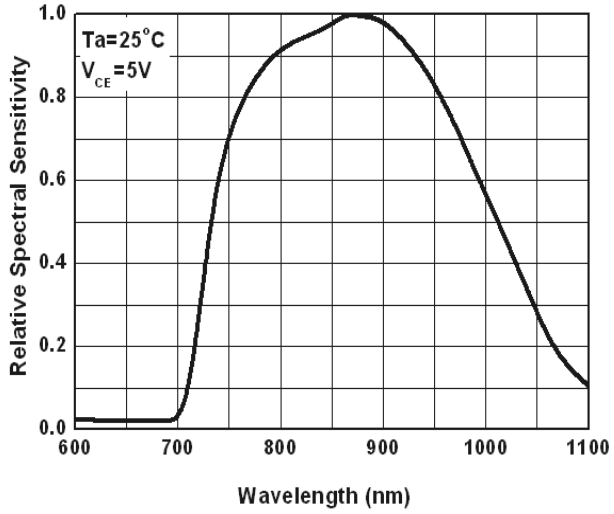


Fig.2 Collector Current vs Irradiance

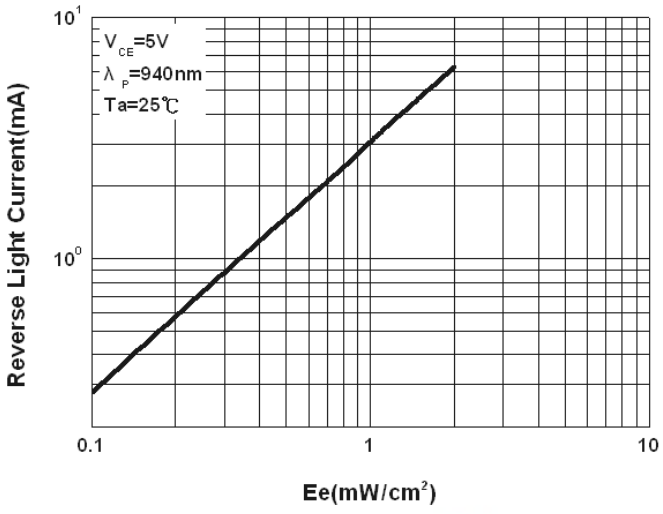


Fig.3 Collector Current vs Collecror-Emitter Voltage

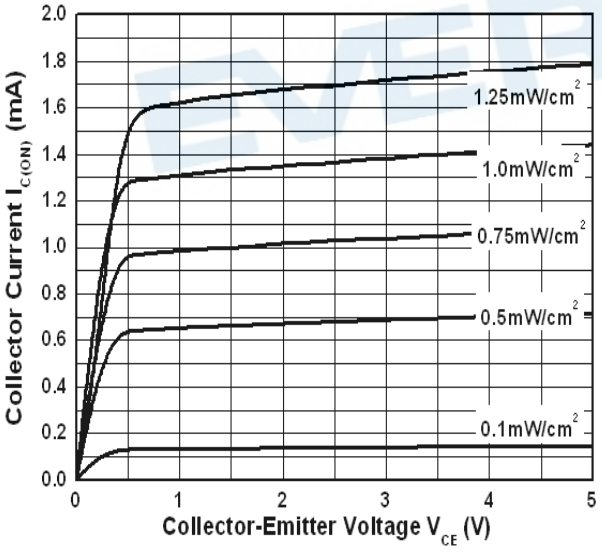


Fig.4 Collector Dark Current vs. Ambient Temperature

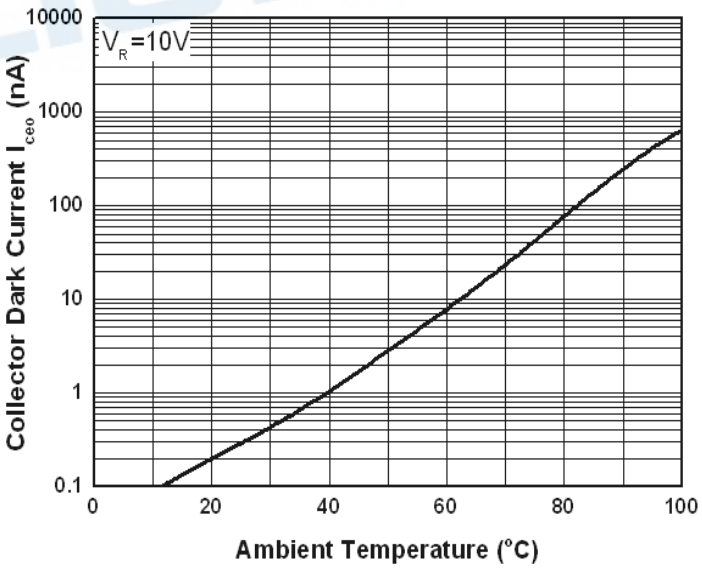
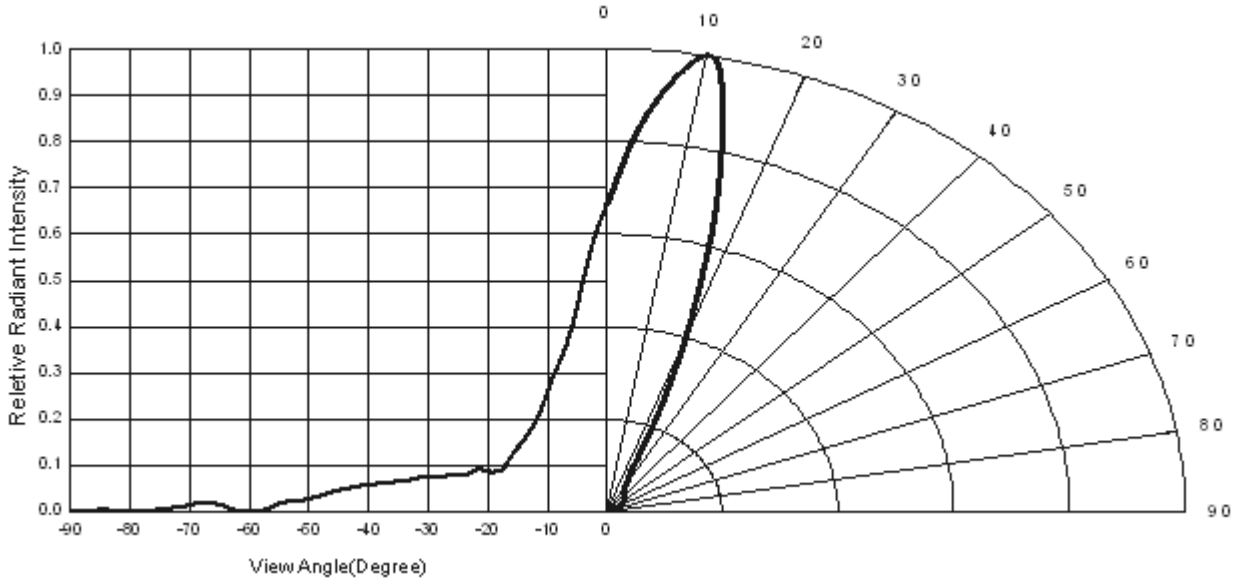


Fig.5 Relative Light Current vs. Angular Displacement



Precautions For Use

1. Over-current-proof

Customer must apply resistors for protection , otherwise slight voltage shift will cause big current change (Burn out will happen).

2. Storage

2.1 Do not open moisture proof bag before the products are ready to use.

2.2 Before opening the package, the Phototransistor should be kept at 30℃ or less and 90%RH or less.

2.3 The Phototransistor should be used within a year.

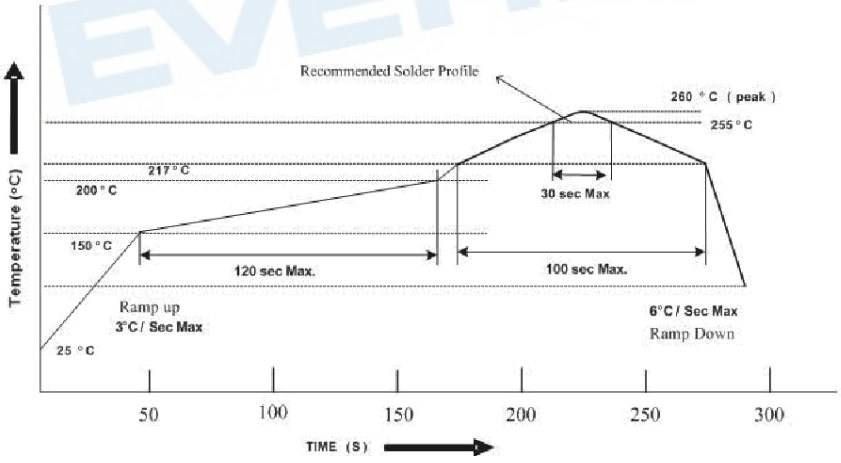
2.4 After opening the package, the Phototransistor should be kept at 30℃ or less and 70%RH or less.

2.5 The Phototransistor should be used within 168 hours (7 days) after opening the package.

2.6 If the moisture absorbent material (silica gel) has faded away or the Phototransistor have exceeded the storage time, baking treatment should be performed using the following conditions.
Baking treatment : 60±5℃ for 24 hours.

3. Soldering Condition

3.1 Pb-free solder temperature profile



3.2 Reflow soldering should not be done more than two times.

3.3 When soldering, do not put stress on the Phototransistor during heating.

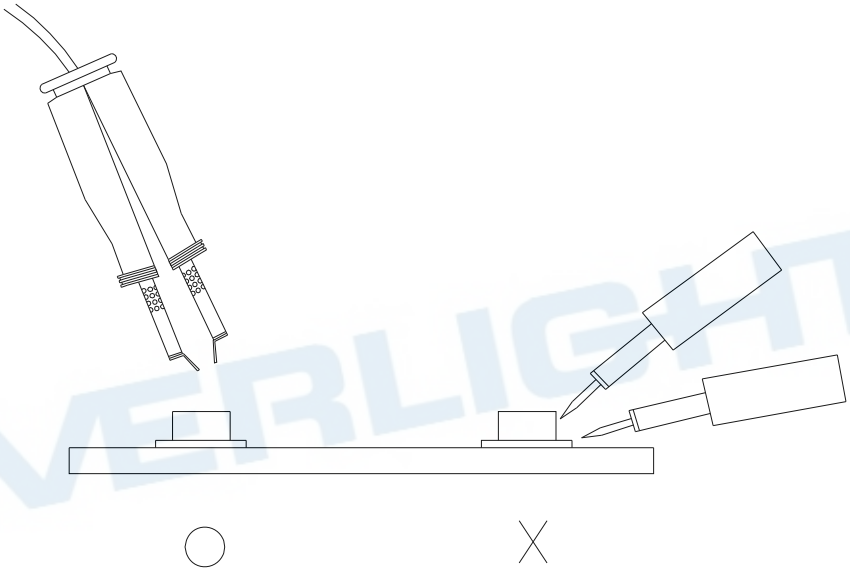
3.4 After soldering, do not warp the circuit board.

4.Soldering Iron

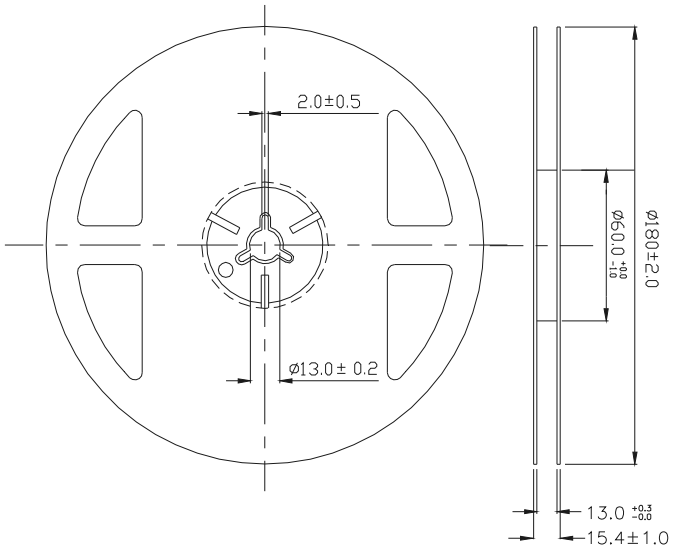
Each terminal is to go to the tip of soldering iron temperature less than 350℃ for 3 seconds within once in less than the soldering iron capacity 25W. Leave two seconds and more intervals, and do soldering of each terminal. Be careful because the damage of the product is often started at the time of the hand solder.

5.Repairing

Repair should not be done after the Phototransistor have been soldered. When repairing is unavoidable, a double-head soldering iron should be used (as below figure). It should be confirmed beforehand whether the characteristics of the Phototransistor will or will not be damaged by repairing.

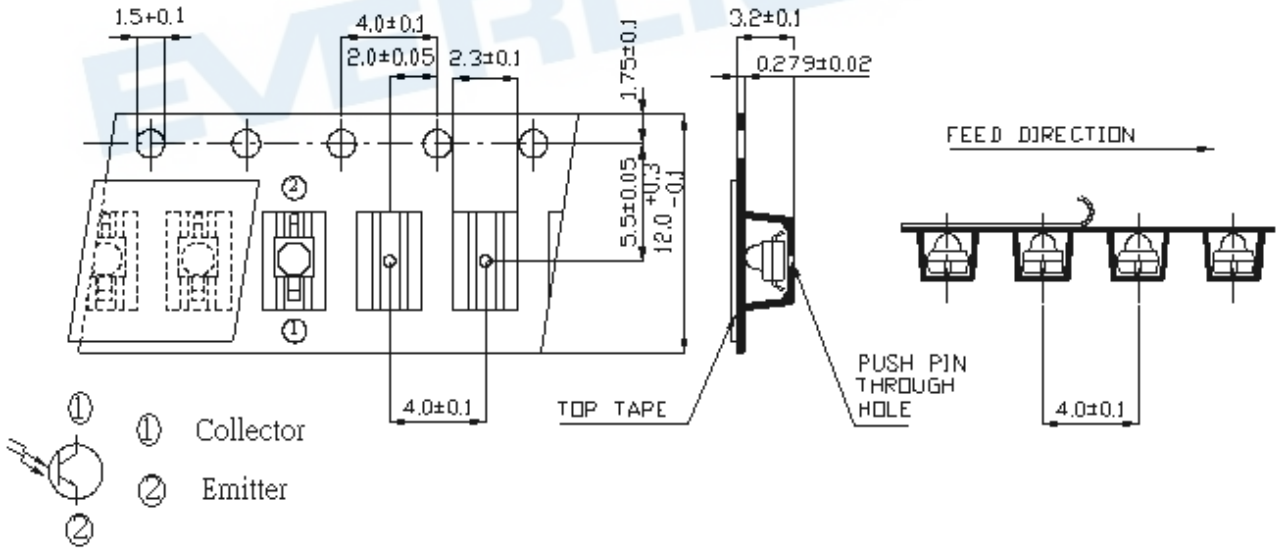


Package Dimensions



Note: The tolerances unless mentioned are ±0.1, unit=mm.

Carrier Taping Dimensions: (Quantity: 1000PCS/Reel)



Note: The tolerances unless mentioned are ±0.1, unit=mm

Label Form Specification

CPN: Customer's Production Number
P/N : Production Number
QTY: Packing Quantity
CAT: Ranks
Peak Wavelength
REF: Reference
LOT No: Lot Number

DISCLAIMER

1. EVERLIGHT reserves the right(s) on the adjustment of product material mix for the specification.
2. The product meets EVERLIGHT published specification for a period of twelve (12) months from date of shipment.
3. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
4. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from the use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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